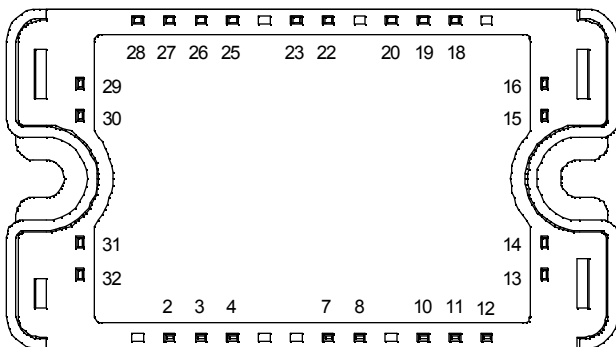
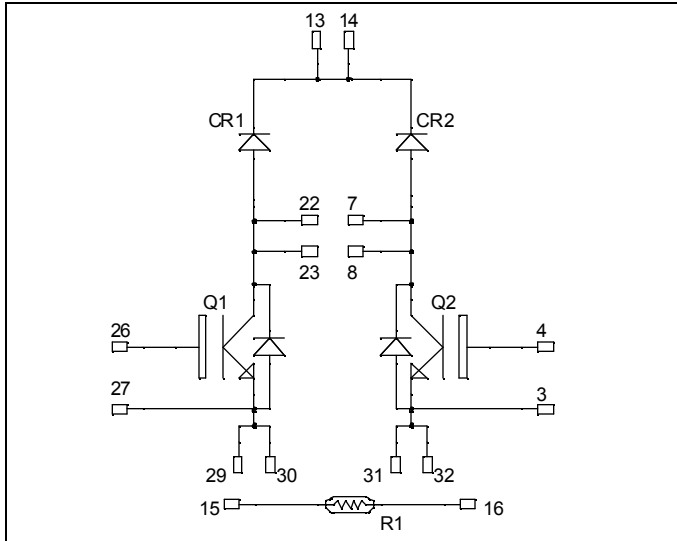


**Dual Boost chopper
Trench + Field Stop IGBT®
Power Module**

www.datasheet4u.com

**$V_{CES} = 600V$
 $I_C = 20A @ T_c = 80^\circ C$**



All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCESat
- Low profile
- Each leg can be easily paralleled to achieve a single boost of twice the current capability.
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	32
		$T_C = 80^\circ C$	20
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	40
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	62
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150^\circ C$	40A @ 550V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 600\text{V}$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 20\text{A}$	$T_j = 25^\circ\text{C}$	1.5	1.9	V
			$T_j = 150^\circ\text{C}$	1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 300\mu\text{A}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			300	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		1100		pF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		70		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		35		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 20\text{A}$ $R_G = 12\Omega$		110		ns
T_r	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			200		
T_f	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 20\text{A}$ $R_G = 12\Omega$		120		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			250		
T_f	Fall Time			60		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 20\text{A}$	$T_j = 25^\circ\text{C}$	0.11		mJ
			$T_j = 150^\circ\text{C}$	0.2		
E_{off}	Turn-off Switching Energy	$R_G = 12\Omega$	$T_j = 25^\circ\text{C}$	0.5		mJ
			$T_j = 150^\circ\text{C}$	0.7		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$		100	μA
			$T_j = 150^\circ\text{C}$		350	
I_F	DC Forward Current		$T_c = 80^\circ\text{C}$	20		A
V_F	Diode Forward Voltage	$I_F = 20\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$	1.6	2	V
			$T_j = 150^\circ\text{C}$	1.5		
t_{rr}	Reverse Recovery Time	$I_F = 20\text{A}$ $V_R = 300\text{V}$ $di/dt = 1600\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	100		ns
			$T_j = 150^\circ\text{C}$	150		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	1.1		μC
			$T_j = 150^\circ\text{C}$	2.3		
E_r	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$	0.23		mJ
			$T_j = 150^\circ\text{C}$	0.50		

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

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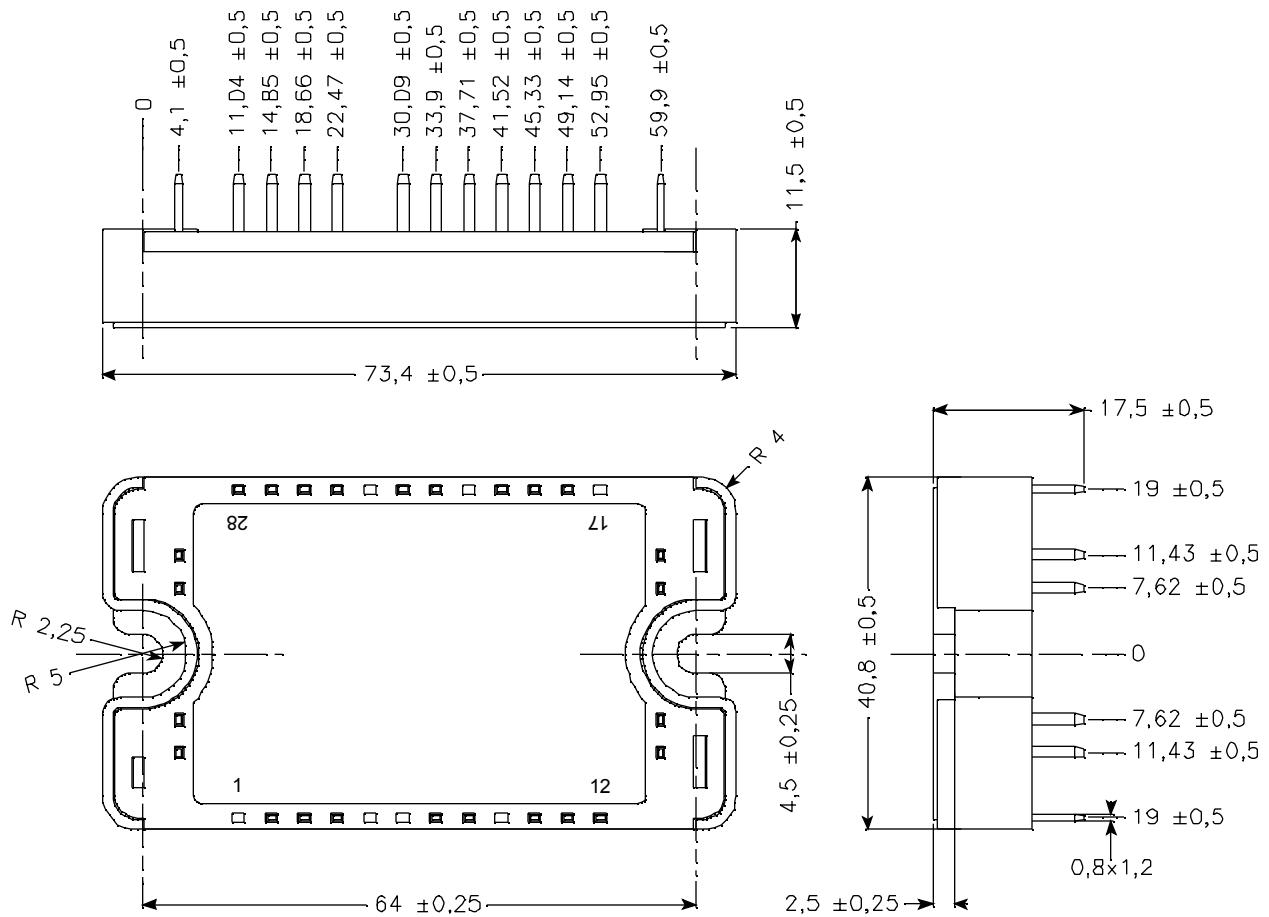
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit		
R _{thJC}	Junction to Case Thermal Resistance	IGBT		2.4	°C/W		
		Diode		3.25			
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V		
T _J	Operating junction temperature range	-40		175	°C		
T _{STG}	Storage Temperature Range	-40		125			
T _C	Operating Case Temperature	-40		100			
Torque	Mounting torque		To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight					110	g

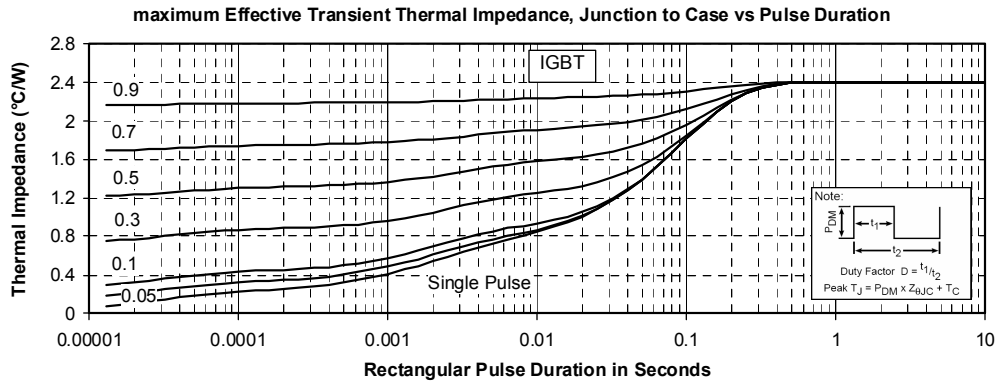
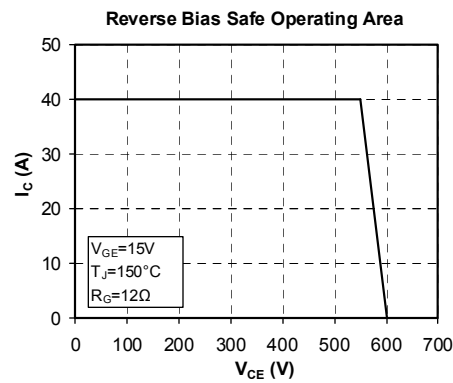
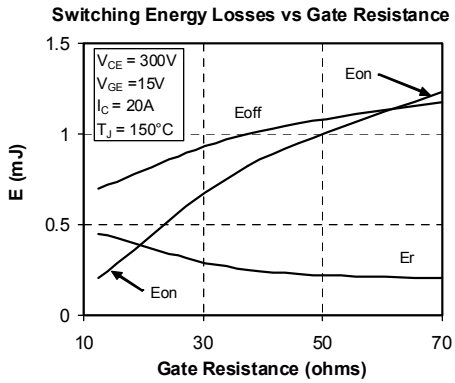
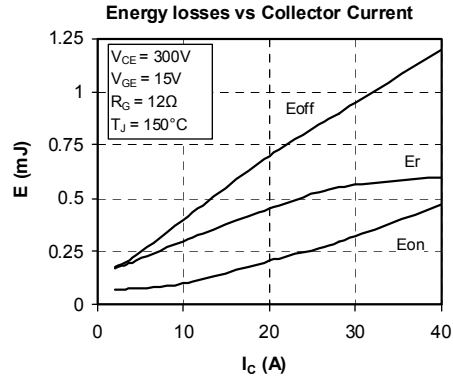
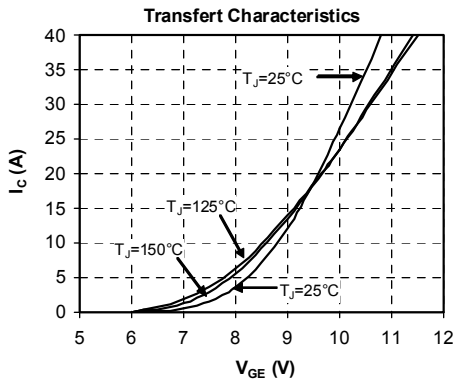
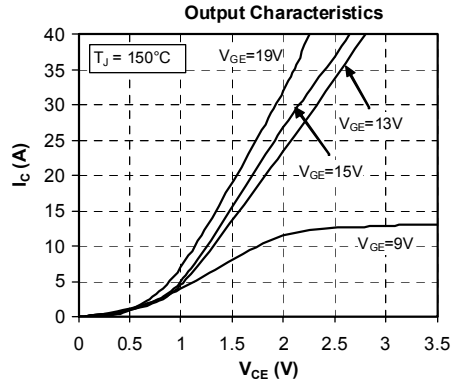
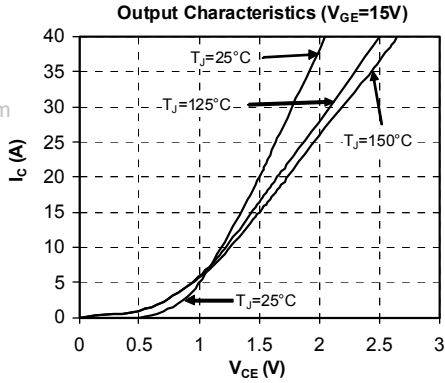
SP3 Package outline (dimensions in mm)



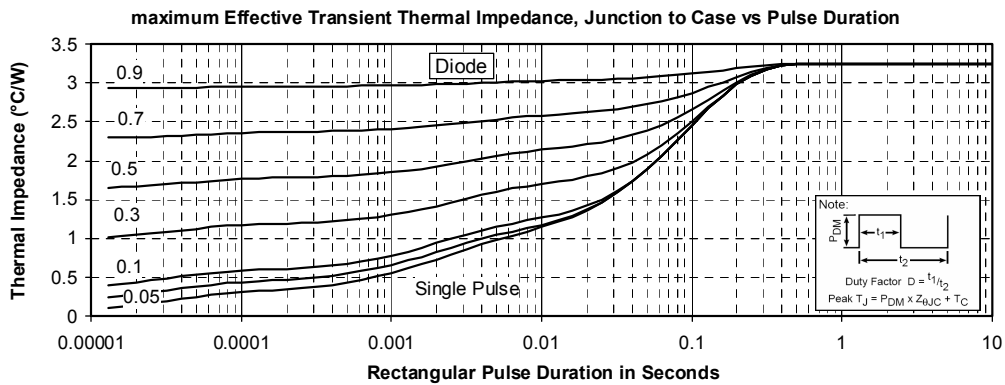
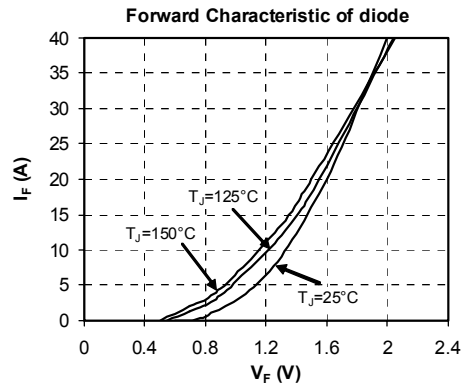
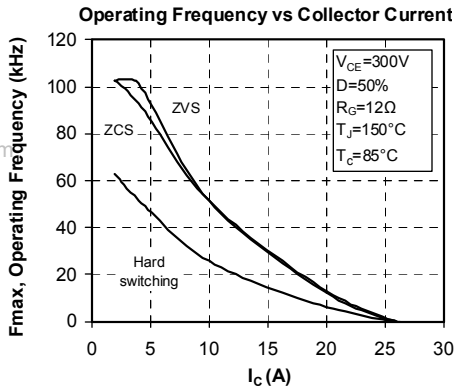
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve

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